L Number	Hits	Search Text	DB	Time stamp
1	260	interface adj level adj density	USPAT;	2004/08/05 22:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	27	(heat adj treatment) near (gate adj	USPAT;	2004/08/05 22:56
		(insulation or insulating or oxide))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	0	(heat adj treatment) near (gate adj	USPAT;	2004/08/05 22:55
		(insulative))	US-PGPUB;	
İ			EPO; JPO;	
			DERWENT;	
_	_		IBM_TDB	
5	0	,	USPAT;	2004/08/05 22:55
		insulant)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
6	0	(heat add treatment) near (see)	IBM_TDB USPAT;	2004/08/05 22:55
°		(heat adj treatment) near (gox)	USPAT; US-PGPUB;	2004/00/03 22:55
			EPO; JPO;	
			DERWENT;	
	İ		IBM TDB	
7	113	temperature near (gate adj (insulation or	USPAT:	2004/08/05 23:04
'	113	insulating or oxide))	US-PGPUB;	2001,00,00 25.01
	ŀ	111041461119 01 011140//	EPO; JPO;	
			DERWENT;	
			IBM TDB	
8	l 0	(heat adj treatment) near (gate adj	USPAT;	2004/08/05 22:56
		dielectric)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
10	0	\	USPAT;	2004/08/05 23:06
		adj insulating)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	•
111		(IBM_TDB	0004/00/05 00:06
11	0	\	USPAT;	2004/08/05 23:06
		adj insulation)	US-PGPUB;	
			EPO; JPO; DERWENT;	·
			IBM TDB	
12	0	 (microwave adj plasma adj cvd) near (gate	USPAT;	2004/08/05 23:06
		adi oxide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
13 -	0	(microwave, adj plasma adj cvd) near (gate	USPAT;	2004/08/05 23:06
		adj dielectric)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	ļ		IBM_TDB	
14	0	(microwave adj plasma adj cvd) near (gate	USPAT;	2004/08/05 23:07
		adj insulative)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1,5			IBM_TDB	2004/00/05 22 27
15	0	(microwave adj plasma adj cvd) near (gox)	USPAT;	2004/08/05 23:07
			US-PGPUB;	
1			EPO; JPO; DERWENT;	
			IBM TDB	
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